

Masataka Hourai

List of Publications by Year in descending order

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68
citing authors

#	ARTICLE	IF	CITATIONS
1	Dependence of the Grown-in Defect Distribution on Growth Rates in Czochralski Silicon. Japanese Journal of Applied Physics, 1993, 32, 3675-3681.	1.5	132
2	Formation of Grown-in Defects during Czochralski Silicon Crystal Growth. Japanese Journal of Applied Physics, 1997, 36, 6595-6600.	1.5	30
3	Formation Behavior of Infrared Light Scattering Defects in Silicon during Czochralski Crystal Growth. Journal of the Electrochemical Society, 1995, 142, 3193-3201.	2.9	27
4	Defect Formation Behaviors in Heavily Doped Czochralski Silicon. ECS Transactions, 2006, 2, 95-107.	0.5	23
5	Relationship between Grown-in Defects in Czochralski Silicon Crystals. Japanese Journal of Applied Physics, 1997, 36, L591-L594.	1.5	22
6	Dependence of Grown-in Defect Behavior on Oxygen Concentration in Czochralski Silicon Crystals. Japanese Journal of Applied Physics, 1999, 38, 5725-5730.	1.5	16
7	Review and Comments for the Development of Point Defect Controlled CZ-Si Crystals and Their Application to Future Power Devices. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800664.	1.8	14
8	Determination of Physical Properties for Point Defects during CZ Silicon Crystal Growth by High-Precision Thermal Simulations. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 2011, 75, 657-664.	0.4	10
9	Oxygen Precipitation Properties of Nitrogen-Doped Czochralski Silicon Single Crystals with Low Oxygen Concentration. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900272.	1.8	9
10	Observation of Ring-OSF Nuclei in CZ-Si Using Short-Time Annealing and Infrared Light Scattering Tomography. Journal of the Electrochemical Society, 1995, 142, 996-1001.	2.9	8
11	Oxygen concentration dependence of as-grown defect formation in nitrogen-doped Czochralski silicon single crystals. Journal of Crystal Growth, 2021, 570, 126236.	1.5	7
12	Recognition and Imaging of Point Defect Diffusion, Recombination, and Reaction During Growth of Czochralski-Silicon Crystals. Journal of Electronic Materials, 2020, 49, 5110-5119.	2.2	2